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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"



Details

Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, SAI, SD, SPDIF-Rx, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	140
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	320K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f746igt7

Contents

1	Description	12
1.1	Full compatibility throughout the family	15
2	Functional overview	17
2.1	ARM [®] Cortex [®] -M7 with FPU	17
2.2	Memory protection unit	17
2.3	Embedded Flash memory	18
2.4	CRC (cyclic redundancy check) calculation unit	18
2.5	Embedded SRAM	18
2.6	AXI-AHB bus matrix	18
2.7	DMA controller (DMA)	19
2.8	Flexible memory controller (FMC)	20
2.9	Quad-SPI memory interface (QUADSPI)	21
2.10	LCD-TFT controller	21
2.11	Chrom-ART Accelerator [™] (DMA2D)	21
2.12	Nested vectored interrupt controller (NVIC)	22
2.13	External interrupt/event controller (EXTI)	22
2.14	Clocks and startup	22
2.15	Boot modes	23
2.16	Power supply schemes	23
2.17	Power supply supervisor	24
2.17.1	Internal reset ON	24
2.17.2	Internal reset OFF	25
2.18	Voltage regulator	26
2.18.1	Regulator ON	26
2.18.2	Regulator OFF	27
2.18.3	Regulator ON/OFF and internal reset ON/OFF availability	30
2.19	Real-time clock (RTC), backup SRAM and backup registers	30
2.20	Low-power modes	31
2.21	V _{BAT} operation	32
2.22	Timers and watchdogs	32
2.22.1	Advanced-control timers (TIM1, TIM8)	34

reached, the option byte loading process starts, either to confirm or modify default BOR thresholds, or to disable BOR permanently. Three BOR thresholds are available through option bytes. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for an external reset circuit.

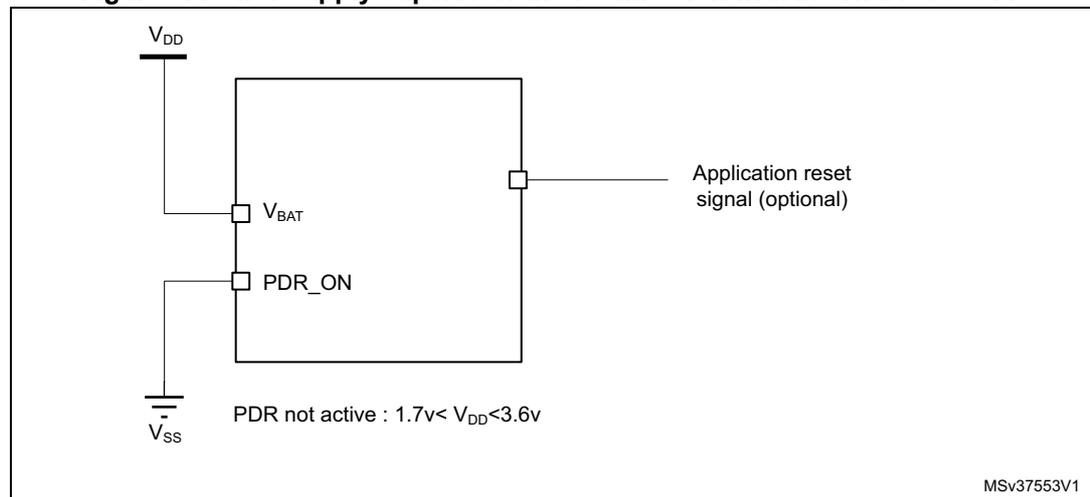
The device also features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

2.17.2 Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled through the PDR_ON pin.

An external power supply supervisor should monitor V_{DD} and should maintain the device in reset mode as long as V_{DD} is below a specified threshold. PDR_ON should be connected to V_{SS} . Refer to [Figure 6: Power supply supervisor interconnection with internal reset OFF](#).

Figure 6. Power supply supervisor interconnection with internal reset OFF



The V_{DD} specified threshold, below which the device must be maintained under reset, is 1.7 V (see [Figure 7](#)).

A comprehensive set of power-saving mode allows to design low-power applications.

When the internal reset is OFF, the following integrated features are no more supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled
- The brownout reset (BOR) circuitry must be disabled
- The embedded programmable voltage detector (PVD) is disabled
- V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD} .

All the packages, except for the LQFP100, allow to disable the internal reset through the PDR_ON signal when connected to V_{SS} .

Table 11. FMC pin definition

Pin name	NOR/PSRAM/SRAM	NOR/PSRAM Mux	NAND16	SDRAM
PF0	A0	-	-	A0
PF1	A1	-	-	A1
PF2	A2	-	-	A2
PF3	A3	-	-	A3
PF4	A4	-	-	A4
PF5	A5	-	-	A5
PF12	A6	-	-	A6
PF13	A7	-	-	A7
PF14	A8	-	-	A8
PF15	A9	-	-	A9
PG0	A10	-	-	A10
PG1	A11	-	-	A11
PG2	A12	-	-	A12
PG3	A13	-	-	-
PG4	A14	-	-	BA0
PG5	A15	-	-	BA1
PD11	A16	A16	CLE	-
PD12	A17	A17	ALE	-
PD13	A18	A18	-	-
PE3	A19	A19	-	-
PE4	A20	A20	-	-
PE5	A21	A21	-	-
PE6	A22	A22	-	-
PE2	A23	A23	-	-
PG13	A24	A24	-	-
PG14	A25	A25	-	-
PD14	D0	DA0	D0	D0
PD15	D1	DA1	D1	D1
PD0	D2	DA2	D2	D2
PD1	D3	DA3	D3	D3
PE7	D4	DA4	D4	D4
PE8	D5	DA5	D5	D5
PE9	D6	DA6	D6	D6
PE10	D7	DA7	D7	D7



Table 12. STM32F745xx and STM32F746xx alternate function mapping

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15	
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/JA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ETH/ OTG1_FS	FMC/SD MMC1/O TG2_FS	DCMI	LCD	SYS	
Port A	PA0	-	TIM2_C H1/TIM2 _ETR	TIM5_C H1	TIM8_ET R	-	-	-	USART2 _CTS	UART4_ TX	-	SAI2_SD_ B	ETH_MII_ CRS	-	-	-	EVEN TOUT	
	PA1	-	TIM2_C H2	TIM5_C H2	-	-	-	-	USART2 _RTS	UART4_ RX	QUADSP I_BK1_IO 3	SAI2_MC K_B	ETH_MII_ RX_CLK/ ETH_RMI I_REF_C LK	-	-	LCD_R2	EVEN TOUT	
	PA2	-	TIM2_C H3	TIM5_C H3	TIM9_CH 1	-	-	-	USART2 _TX	SAI2_SC K_B	-	-	ETH_MDI O	-	-	LCD_R1	EVEN TOUT	
	PA3	-	TIM2_C H4	TIM5_C H4	TIM9_CH 2	-	-	-	USART2 _RX	-	-	OTG_HS_ ULPI_D0	ETH_MII_ COL	-	-	LCD_B5	EVEN TOUT	
	PA4	-	-	-	-	-	-	SPI1_NS S/I2S1_ WS	SPI3_NS S/I2S3_ WS	USART2 _CK	-	-	-	OTG_HS_ _SOF	DCMI_H SYNC	LCD_VS YNC	EVEN TOUT	
	PA5	-	TIM2_C H1/TIM2 _ETR	-	TIM8_CH 1N	-	-	SPI1_SC K/I2S1_ CK	-	-	-	-	OTG_HS_ ULPI_CK	-	-	-	LCD_R4	EVEN TOUT
	PA6	-	TIM1_B KIN	TIM3_C H1	TIM8_BKI N	-	-	SPI1_MI SO	-	-	-	TIM13_C H1	-	-	-	DCMI_PI XCLK	LCD_G2	EVEN TOUT
	PA7	-	TIM1_C H1N	TIM3_C H2	TIM8_CH 1N	-	-	SPI1_M OSI/I2S1 _SD	-	-	-	TIM14_C H1	-	ETH_MII_ RX_DV/E TH_RMII_ CRS_DV	FMC_SD NWE	-	-	EVEN TOUT
	PA8	MCO1	TIM1_C H1	-	TIM8_BKI N2	I2C3_SC L	-	-	-	USART1 _CK	-	-	OTG_FS_ SOF	-	-	-	LCD_R6	EVEN TOUT
	PA9	-	TIM1_C H2	-	-	I2C3_SM BA	SPI2_SC K/I2S2_ CK	-	-	USART1 _TX	-	-	-	-	-	DCMI_D 0	-	EVEN TOUT
	PA10	-	TIM1_C H3	-	-	-	-	-	-	USART1 _RX	-	-	OTG_FS_ ID	-	-	DCMI_D 1	-	EVEN TOUT
PA11	-	TIM1_C H4	-	-	-	-	-	-	USART1 _CTS	-	CAN1_R X	OTG_FS_ DM	-	-	-	LCD_R4	EVEN TOUT	



Table 12. STM32F745xx and STM32F746xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ETH/ OTG1_FS	FMC/SD MMC1/O TG2_FS	DCMI	LCD	SYS
Port B	PB9	-	-	TIM4_C H4	TIM11_CH 1	I2C1_SD A	SPI2_NS S/I2S2_ WS	-	-	-	CAN1_T X	-	-	SDMMC 1_D5	DCMI_D 7	LCD_B7	EVEN TOUT
	PB10	-	TIM2_C H3	-	-	I2C2_SC L	SPI2_SC K/I2S2_ CK	-	USART3 _TX	-	-	OTG_HS_ ULPI_D3	ETH_MII_ RX_ER	-	-	LCD_G4	EVEN TOUT
	PB11	-	TIM2_C H4	-	-	I2C2_SD A	-	-	USART3 _RX	-	-	OTG_HS_ ULPI_D4	ETH_MII_ TX_EN/ ETH_RMII_ TX_EN	-	-	LCD_G5	EVEN TOUT
	PB12	-	TIM1_B KIN	-	-	I2C2_SM BA	SPI2_NS S/I2S2_ WS	-	USART3 _CK	-	CAN2_R X	OTG_HS_ ULPI_D5	ETH_MII_ TXD0/ET H_RMII_T XD0	OTG_HS _ID	-	-	EVEN TOUT
	PB13	-	TIM1_C H1N	-	-	-	SPI2_SC K/I2S2_ CK	-	USART3 _CTS	-	CAN2_T X	OTG_HS_ ULPI_D6	ETH_MII_ TXD1/ET H_RMII_T XD1	-	-	-	EVEN TOUT
	PB14	-	TIM1_C H2N	-	TIM8_CH 2N	-	SPI2_MI SO	-	USART3 _RTS	-	TIM12_C H1	-	-	OTG_HS _DM	-	-	EVEN TOUT
	PB15	RTC_R EFIN	TIM1_C H3N	-	TIM8_CH 3N	-	SPI2_M OSI/I2S2 _SD	-	-	-	-	TIM12_C H2	-	OTG_HS _DP	-	-	EVEN TOUT
Port C	PC0	-	-	-	-	-	-	-	-	SAI2_FS _B	-	OTG_HS_ ULPI_ST P	-	FMC_SD NWE	-	LCD_R5	EVEN TOUT
	PC1	TRACE D0	-	-	-	-	SPI2_M OSI/I2S2 _SD	SAI1_SD _A	-	-	-	-	ETH_MD C	-	-	-	EVEN TOUT
	PC2	-	-	-	-	-	SPI2_MI SO	-	-	-	-	OTG_HS_ ULPI_DIR	ETH_MII_ TXD2	FMC_SD NE0	-	-	EVEN TOUT
	PC3	-	-	-	-	-	SPI2_M OSI/I2S2 _SD	-	-	-	-	OTG_HS_ ULPI_NX T	ETH_MII_ TX_CLK	FMC_SD CKE0	-	-	EVEN TOUT



Table 12. STM32F745xx and STM32F746xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15	
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ETH/ OTG1_FS	FMC/SD MMC1/O TG2_FS	DCMI	LCD	SYS	
Port D	PD14	-	-	TIM4_C H3	-	-	-	-	-	UART8_ CTS	-	-	-	FMC_D0	-	-	EVEN TOUT	
	PD15	-	-	TIM4_C H4	-	-	-	-	-	UART8_ RTS	-	-	-	FMC_D1	-	-	EVEN TOUT	
Port E	PE0	-	-	TIM4_ET R	LPTIM1_E TR	-	-	-	-	UART8_ Rx	-	SAI2_MC K_A	-	FMC_NB L0	DCMI_D 2	-	EVEN TOUT	
	PE1	-	-	-	LPTIM1_I N2	-	-	-	-	UART8_T x	-	-	-	FMC_NB L1	DCMI_D 3	-	EVEN TOUT	
	PE2	TRACE CLK	-	-	-	-	SPI4_SC K	SAI1_M CLK_A	-	-	QUADSP I_BK1_IO 2	-	ETH_MII_ TXD3	FMC_A2 3	-	-	EVEN TOUT	
	PE3	TRACE D0	-	-	-	-	-	SAI1_SD _B	-	-	-	-	-	FMC_A1 9	-	-	EVEN TOUT	
	PE4	TRACE D1	-	-	-	-	SPI4_NS S	SAI1_FS _A	-	-	-	-	-	FMC_A2 0	DCMI_D 4	LCD_B0	EVEN TOUT	
	PE5	TRACE D2	-	-	TIM9_CH 1	-	SPI4_MI SO	SAI1_SC K_A	-	-	-	-	-	FMC_A2 1	DCMI_D 6	LCD_G0	EVEN TOUT	
	PE6	TRACE D3	TIM1_B KIN2	-	TIM9_CH 2	-	SPI4_M OSI	SAI1_SD _A	-	-	-	-	SAI2_MC K_B	-	FMC_A2 2	DCMI_D 7	LCD_G1	EVEN TOUT
	PE7	-	TIM1_ET R	-	-	-	-	-	-	UART7_ Rx	-	QUADSPI _BK2_IO0	-	FMC_D4	-	-	EVEN TOUT	
	PE8	-	TIM1_C H1N	-	-	-	-	-	-	UART7_T x	-	QUADSPI _BK2_IO1	-	FMC_D5	-	-	EVEN TOUT	
	PE9	-	TIM1_C H1	-	-	-	-	-	-	UART7_ RTS	-	QUADSPI _BK2_IO2	-	FMC_D6	-	-	EVEN TOUT	
	PE10	-	TIM1_C H2N	-	-	-	-	-	-	UART7_ CTS	-	QUADSPI _BK2_IO3	-	FMC_D7	-	-	EVEN TOUT	
	PE11	-	TIM1_C H2	-	-	-	SPI4_NS S	-	-	-	-	SAI2_SD_ B	-	FMC_D8	-	LCD_G3	EVEN TOUT	
	PE12	-	TIM1_C H3N	-	-	-	SPI4_SC K	-	-	-	-	SAI2_SC K_B	-	FMC_D9	-	LCD_B4	EVEN TOUT	
	PE13	-	TIM1_C H3	-	-	-	SPI4_MI SO	-	-	-	-	SAI2_FS_ B	-	FMC_D1 0	-	LCD_DE	EVEN TOUT	

Table 13. STM32F745xx and STM32F746xx register boundary addresses (continued)

Bus	Boundary address	Peripheral
	0x4001 6C00 - 0x4001 FFFF	Reserved
APB2	0x4001 6800 - 0x4001 6BFF	LCD-TFT
	0x4001 6000 - 0x4001 67FF	Reserved
	0x4001 5C00 - 0x4001 5FFF	SAI2
	0x4001 5800 - 0x4001 5BFF	SAI1
	0x4001 5400 - 0x4001 57FF	SPI6
	0x4001 5000 - 0x4001 53FF	SPI5
	0x4001 4C00 - 0x4001 4FFF	Reserved
	0x4001 4800 - 0x4001 4BFF	TIM11
	0x4001 4400 - 0x4001 47FF	TIM10
	0x4001 4000 - 0x4001 43FF	TIM9
	0x4001 3C00 - 0x4001 3FFF	EXTI
	0x4001 3800 - 0x4001 3BFF	SYSCFG
	0x4001 3400 - 0x4001 37FF	SPI4
	0x4001 3000 - 0x4001 33FF	SPI1/I2S1
	0x4001 2C00 - 0x4001 2FFF	SDMMC
	0x4001 2400 - 0x4001 2BFF	Reserved
	0x4001 2000 - 0x4001 23FF	ADC1 - ADC2 - ADC3
	0x4001 1800 - 0x4001 1FFF	Reserved
	0x4001 1400 - 0x4001 17FF	USART6
	0x4001 1000 - 0x4001 13FF	USART1
	0x4001 0800 - 0x4001 0FFF	Reserved
	0x4001 0400 - 0x4001 07FF	TIM8
0x4001 0000 - 0x4001 03FF	TIM1	

Table 17. General operating conditions (continued)

Symbol	Parameter	Conditions ⁽¹⁾	Min	Typ	Max	Unit
V ₁₂	Regulator ON: 1.2 V internal voltage on V _{CAP_1} /V _{CAP_2} pins	Power Scale 3 ((VOS[1:0] bits in PWR_CR register = 0x01), 144 MHz HCLK max frequency)	1.08	1.14	1.20	V
		Power Scale 2 ((VOS[1:0] bits in PWR_CR register = 0x10), 168 MHz HCLK max frequency with over-drive OFF or 180 MHz with over-drive ON)	1.20	1.26	1.32	
		Power Scale 1 ((VOS[1:0] bits in PWR_CR register = 0x11), 180 MHz HCLK max frequency with over-drive OFF or 216 MHz with over-drive ON)	1.26	1.32	1.40	
	Regulator OFF: 1.2 V external voltage must be supplied from external regulator on V _{CAP_1} /V _{CAP_2} pins ⁽⁷⁾	Max frequency 144 MHz	1.10	1.14	1.20	
		Max frequency 168MHz	1.20	1.26	1.32	
		Max frequency 180 MHz	1.26	1.32	1.38	
V _{IN}	Input voltage on RST and FT pins ⁽⁸⁾	2 V ≤ V _{DD} ≤ 3.6 V	- 0.3	-	5.5	
		V _{DD} ≤ 2 V	- 0.3	-	5.2	
	Input voltage on TTa pins	-	- 0.3	-	V _{DDA+} 0.3	
	Input voltage on BOOT pin	-	0	-	9	
P _D	Power dissipation at T _A = 85 °C for suffix 6 or T _A = 105 °C for suffix 7 ⁽⁹⁾	LQFP100	-	-	465	mW
		TFBGA100	-	-	351	
		WLCSP143	-	-	641	
		LQFP144	-	-	500	
		LQFP176	-	-	526	
		UFBGA176	-	-	513	
		LQFP208	-	-	1053	
		TFBGA216	-	-	690	
T _A	Ambient temperature for 6 suffix version	Maximum power dissipation	- 40	-	85	°C
		Low power dissipation ⁽¹⁰⁾	- 40	-	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	- 40	-	105	°C
		Low power dissipation ⁽¹⁰⁾	- 40	-	125	
T _J	Junction temperature range	6 suffix version	- 40	-	105	°C
		7 suffix version	- 40	-	125	

1. The over-drive mode is not supported at the voltage ranges from 1.7 to 2.1 V.
2. 216 MHz maximum frequency for 6 suffix version (200 MHz maximum frequency for 7 suffix version).
3. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to [Section 2.17.2: Internal reset OFF](#)).
4. When the ADC is used, refer to [Table 62: ADC characteristics](#).
5. If V_{REF+} pin is present, it must respect the following condition: V_{DDA}-V_{REF+} < 1.2 V.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load).
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted both to f_{HCLK} frequency and V_{DD} range (see [Table 18: Limitations depending on the operating power supply range](#)).
- When the regulator is ON, the voltage scaling and over-drive mode are adjusted to f_{HCLK} frequency as follows:
 - Scale 3 for f_{HCLK} ≤ 144 MHz
 - Scale 2 for 144 MHz < f_{HCLK} ≤ 168 MHz
 - Scale 1 for 168 MHz < f_{HCLK} ≤ 216 MHz. The over-drive is only ON at 216 MHz.
- When the regulator is OFF, the V12 is provided externally as described in [Table 17: General operating conditions](#):
- The system clock is HCLK, f_{PCLK1} = f_{HCLK}/4, and f_{PCLK2} = f_{HCLK}/2.
- External clock frequency is 25 MHz and PLL is ON when f_{HCLK} is higher than 25 MHz.
- The typical current consumption values are obtained for 1.7 V ≤ V_{DD} ≤ 3.6 V voltage range and for T_A = 25 °C unless otherwise specified.
- The maximum values are obtained for 1.7 V ≤ V_{DD} ≤ 3.6 V voltage range and a maximum ambient temperature (T_A) unless otherwise specified.
- For the voltage range 1.7 V ≤ V_{DD} ≤ 3.6 V, the maximum frequency is 180 MHz.

Table 24. Typical and maximum current consumption in Run mode, code with data processing running from ITCM RAM, regulator ON

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
					T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in RUN mode	All peripherals enabled ⁽²⁾⁽³⁾	216	178	208 ⁽⁴⁾	230 ⁽⁴⁾	-	mA
			200	165	193	212	230	
			180	147	171 ⁽⁴⁾	185 ⁽⁴⁾	198 ⁽⁴⁾	
			168	130	152	164	177	
			144	100	116	127	137	
			60	44	52	63	73	
			25	21	25	36	46	
		All peripherals disabled ⁽³⁾	216	102	120 ⁽⁴⁾	141 ⁽⁴⁾	-	
			200	95	111	131	149	
			180	84	98 ⁽⁴⁾	112 ⁽⁴⁾	125 ⁽⁴⁾	
			168	75	87	100	112	
			144	58	67	77	88	
			60	25	30	41	51	
			25	12	15	25	36	

1. Guaranteed by characterization results.

Table 33. Typical and maximum current consumptions in V_{BAT} mode

Symbol	Parameter	Conditions ⁽¹⁾	Typ			Max ⁽²⁾		Unit
			T _A =25 °C			T _A =85 °C	T _A =105 °C	
			V _{BAT} = 1.7 V	V _{BAT} = 2.4 V	V _{BAT} = 3.3 V	V _{BAT} = 3.6 V		
I _{DD_VBAT}	Supply current in V _{BAT} mode	Backup SRAM OFF, RTC and LSE OFF	0.03	0.03	0.04	0.2	0.4	μA
		Backup SRAM ON, RTC and LSE OFF	0.74	0.75	0.78	3.0	7.0	
		Backup SRAM OFF, RTC ON and LSE in low drive mode	0.40	0.52	0.72	2.8	6.5	
		Backup SRAM OFF, RTC ON and LSE in medium low drive mode	0.40	0.52	0.72	2.8	6.5	
		Backup SRAM OFF, RTC ON and LSE in medium high drive mode	0.54	0.64	0.85	3.3	7.6	
		Backup SRAM OFF, RTC ON and LSE in high drive mode	0.62	0.73	0.94	3.6	8.4	
		Backup SRAM ON, RTC ON and LSE in low drive mode	1.06	1.18	1.41	5.4	12.7	
		Backup SRAM ON, RTC ON and LSE in Medium low drive mode	1.16	1.28	1.51	5.8	13.6	
		Backup SRAM ON, RTC ON and LSE in Medium high drive mode	1.18	1.3	1.54	5.9	13.8	
		Backup SRAM ON, RTC ON and LSE in High drive mode	1.36	1.48	1.73	6.7	15.5	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a C_L of 6 pF for typical values.

2. Guaranteed by characterization results.

Figure 27. Typical V_{BAT} current consumption (RTC ON/BKP SRAM OFF and LSE in medium high drive mode)

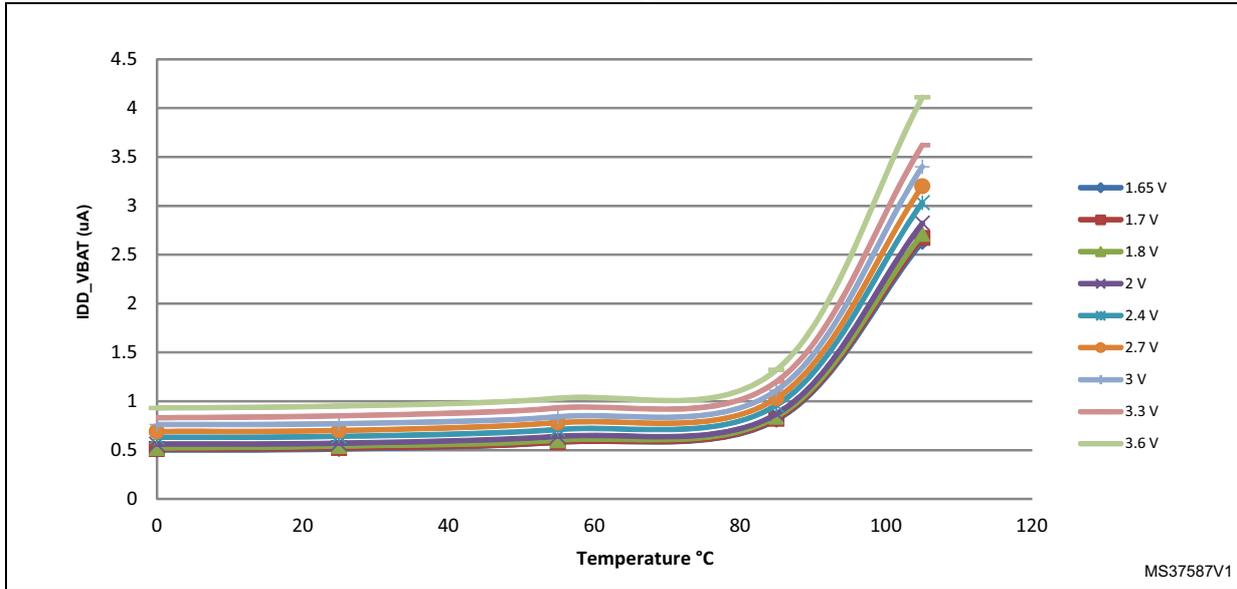


Figure 28. Typical V_{BAT} current consumption (RTC ON/BKP SRAM OFF and LSE in high drive mode)

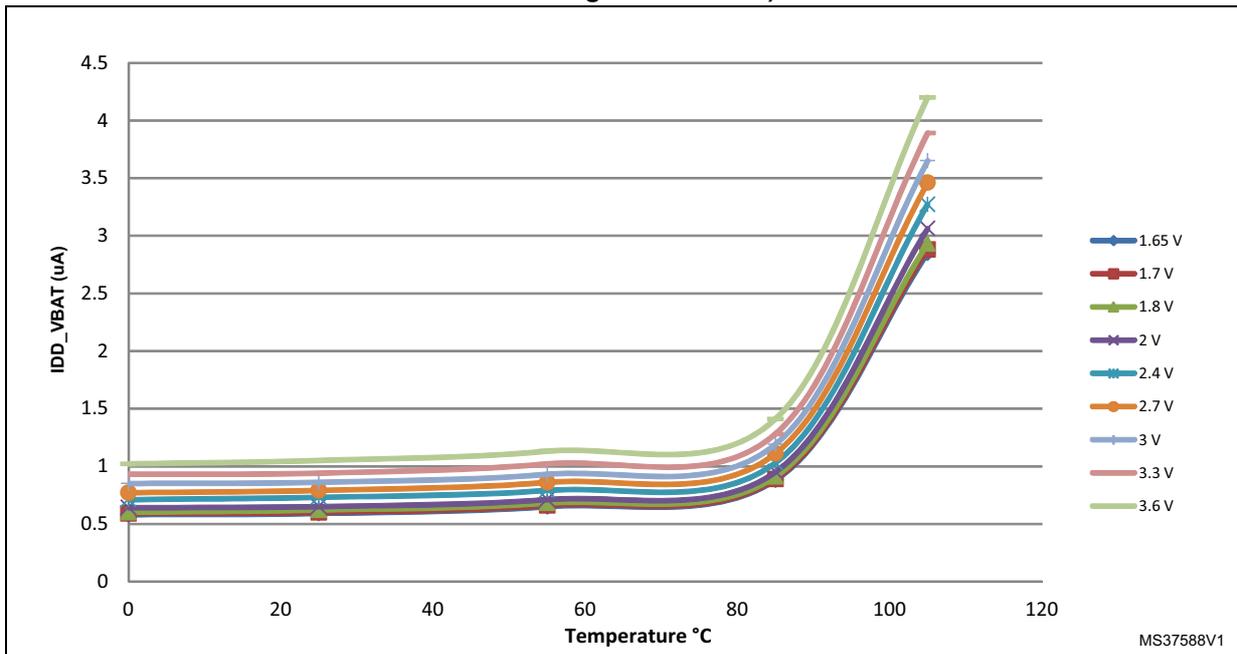
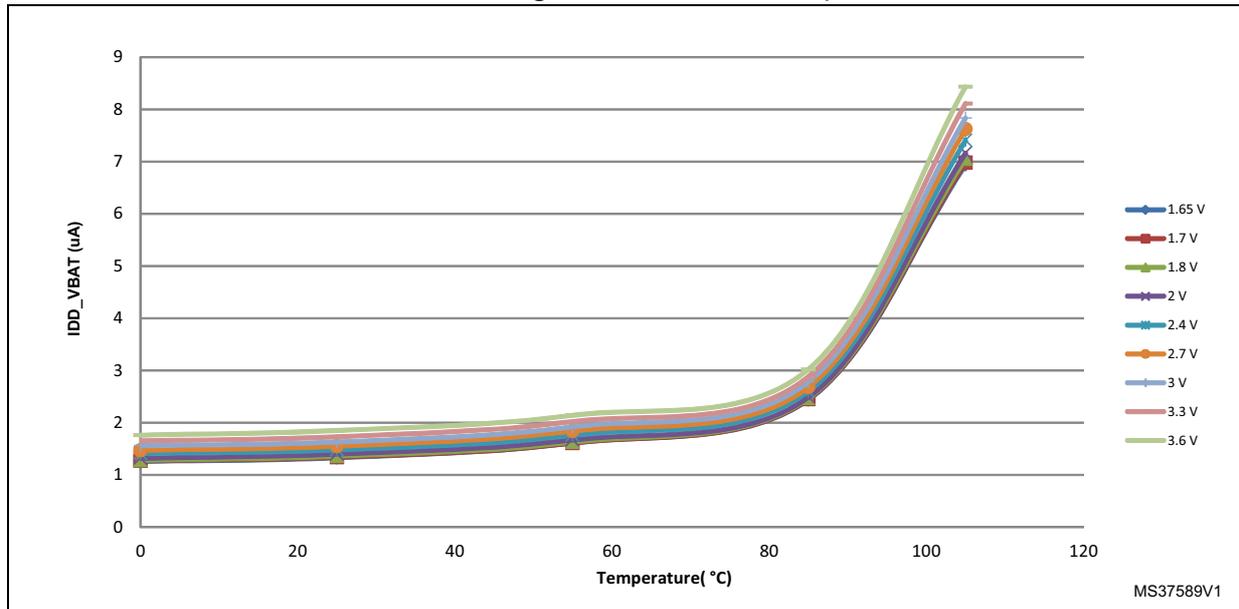


Figure 29. Typical V_{BAT} current consumption (RTC ON/BKP SRAM OFF and LSE in high medium drive mode)



I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in [Table 56: I/O static characteristics](#).

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

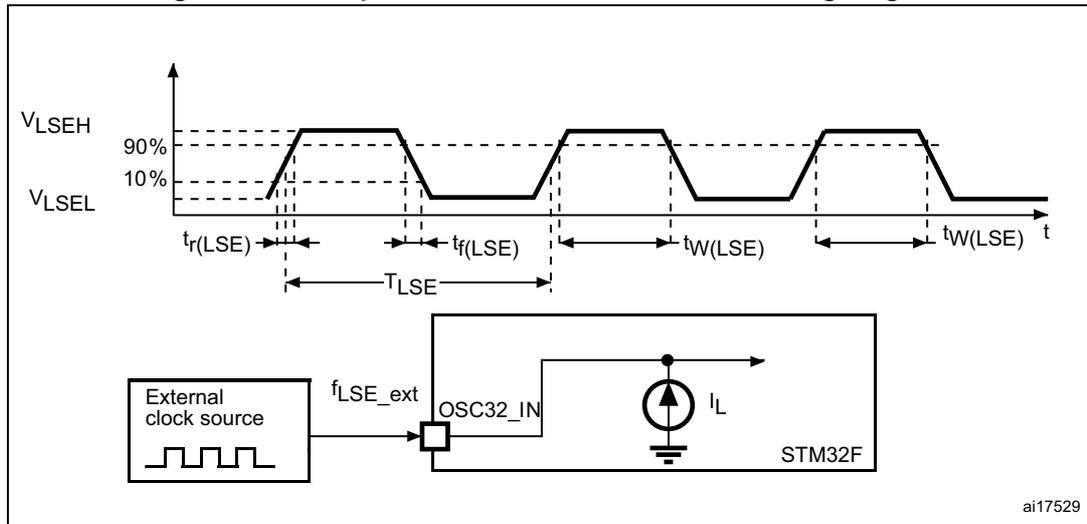
Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see [Table 35: Peripheral current consumption](#)), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O

Figure 31. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 39](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 39. HSE 4-26 MHz oscillator characteristics⁽¹⁾

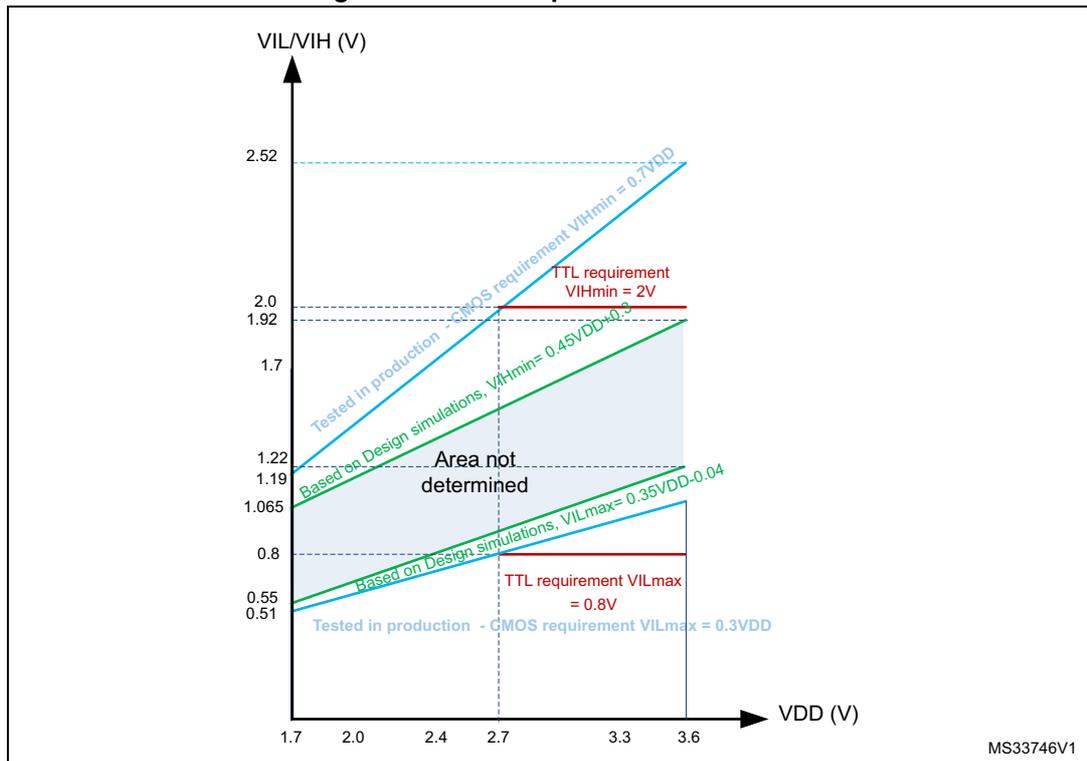
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f _{OSC_IN}	Oscillator frequency	-	4	-	26	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
I _{DD}	HSE current consumption	V _{DD} =3.3 V, ESR= 30 Ω, C _L =5 pF@25 MHz	-	450	-	μA
		V _{DD} =3.3 V, ESR= 30 Ω, C _L =10 pF@25 MHz	-	530	-	
ACC _{HSE} ⁽²⁾	HSE accuracy	-	- 500	-	500	ppm
G _{m_crit_max}	Maximum critical crystal g _m	Startup	-	-	1	mA/V
t _{SU(HSE)} ⁽³⁾	Startup time	V _{DD} is stabilized	-	2	-	ms

1. Guaranteed by design.
2. This parameter depends on the crystal used in the application. The minimum and maximum values must be respected to comply with USB standard specifications.
3. t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is based on characterization results. It is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

7. Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
8. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT I/Os is shown in [Figure 38](#).

Figure 38. FT I/O input characteristics



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14, PC15 and PI8 which can sink or source up to ± 3 mA. When using the PC13 to PC15 and PI8 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 5.2](#). In particular:

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating ΣI_{VDD} (see [Table 15](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see [Table 15](#)).

Table 58. I/O AC characteristics⁽¹⁾⁽²⁾ (continued)

OSPEEDRy [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
11	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 30 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	100 ⁽⁴⁾	MHz
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	50	
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	42.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	180 ⁽⁴⁾	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	100	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	72.5	
	$t_{f(\text{IO})\text{out}}/ t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 30 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	4	ns
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	6	
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	7	
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	2.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	3.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	4	
-	$t_{\text{EXTI}pw}$	Pulse width of external signals detected by the EXTI controller	-	10	-	-	ns

1. Guaranteed by design.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F75xxx and STM32F74xxx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in [Figure 39](#).
4. For maximum frequencies above 50 MHz and $V_{DD} > 2.4 \text{ V}$, the compensation cell should be used.

Figure 39. I/O AC characteristics definition

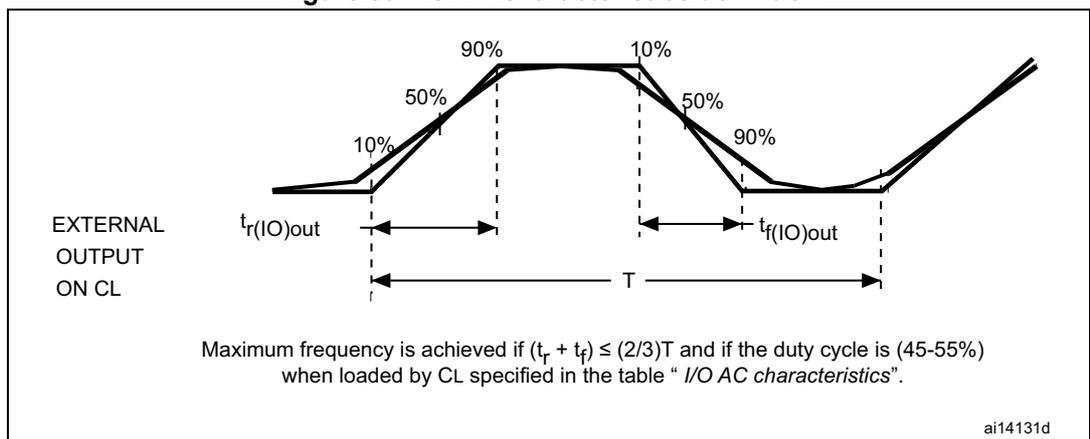


Figure 47. SPI timing diagram - slave mode and CPHA = 1

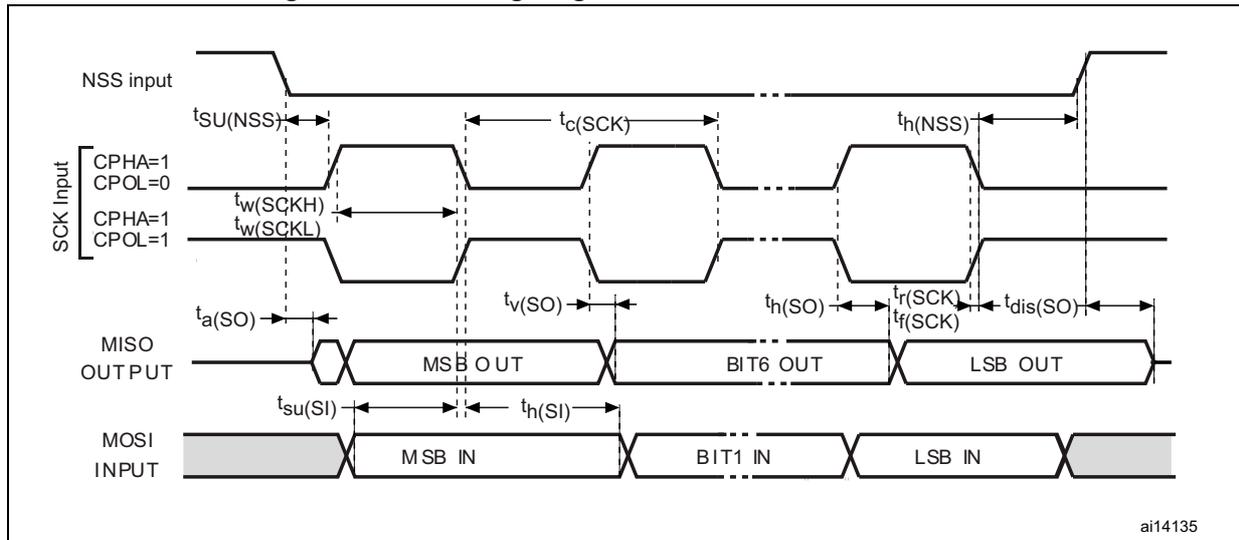
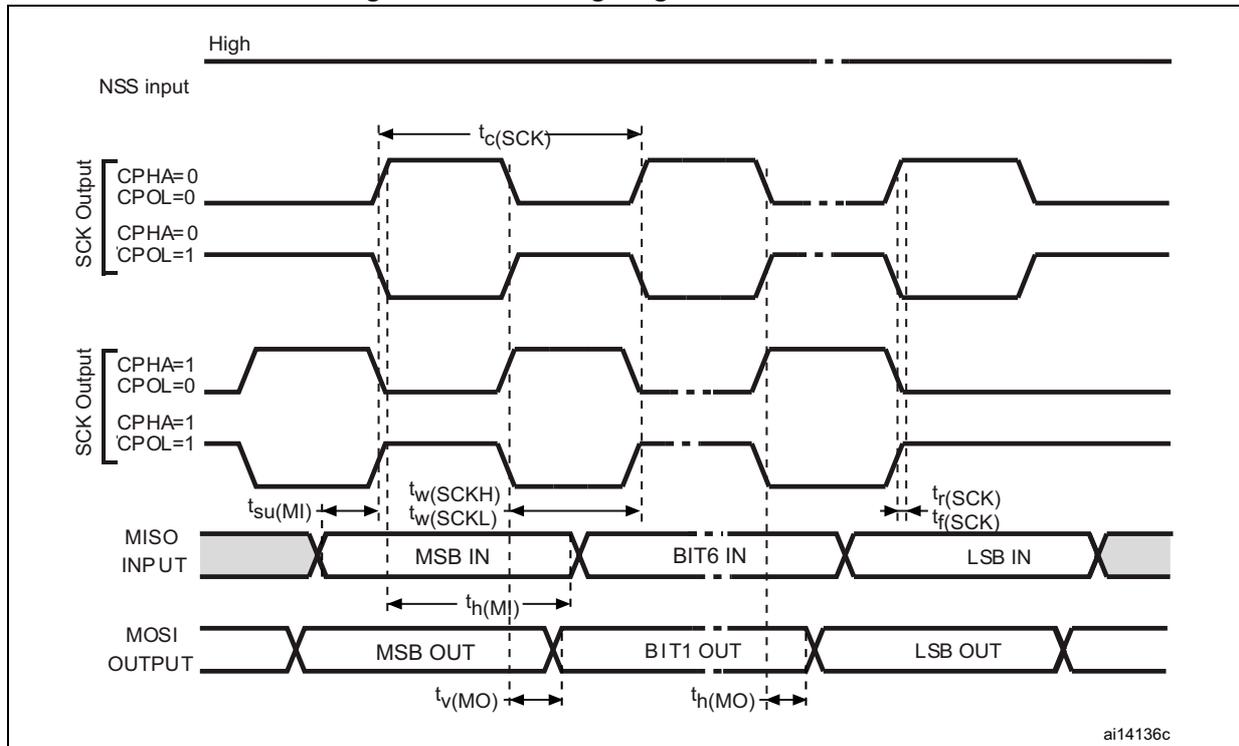


Figure 48. SPI timing diagram - master mode



I²S interface characteristics

Unless otherwise specified, the parameters given in [Table 77](#) for the I²S interface are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 17](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Table 83. USB HS clock timing parameters⁽¹⁾

Symbol	Parameter		Min	Typ	Max	Unit
-	f _{HCLK} value to guarantee proper operation of USB HS interface		30	-	-	MHz
F _{START_8BIT}	Frequency (first transition)	8-bit ±10%	54	60	66	MHz
F _{STEADY}	Frequency (steady state) ±500 ppm		59.97	60	60.03	MHz
D _{START_8BIT}	Duty cycle (first transition)	8-bit ±10%	40	50	60	%
D _{STEADY}	Duty cycle (steady state) ±500 ppm		49.975	50	50.025	%
t _{STEADY}	Time to reach the steady state frequency and duty cycle after the first transition		-	-	1.4	ms
t _{START_DEV}	Clock startup time after the de-assertion of SuspendM	Peripheral	-	-	5.6	ms
t _{START_HOST}		Host	-	-	-	
t _{PREP}	PHY preparation time after the first transition of the input clock		-	-	-	µs

1. Guaranteed by design.

Figure 54. ULPI timing diagram

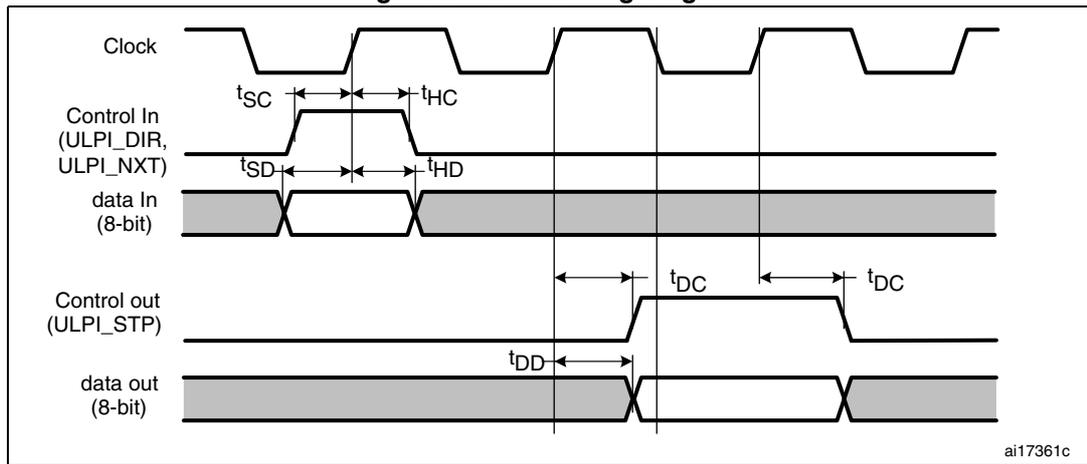


Table 99. Synchronous non-multiplexed PSRAM write timings⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_{(CLK)}$	FMC_CLK period	$2T_{HCLK}-1$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	2.5	
$t_{(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0...2)	$T_{HCLK}+0.5$	-	
$t_{d(CLKL-NADV L)}$	FMC_CLK low to FMC_NADV low	-	1.5	
$t_{d(CLKL-NADV H)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16...25)	-	2.5	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16...25)	0	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	1.5	
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK}+1$	-	
$t_{d(CLKL-Data)}$	FMC_D[15:0] valid data after FMC_CLK low	-	3	
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	1.5	-	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK}+0.5$	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	3.5	-	

1. Guaranteed by characterization results.

NAND controller waveforms and timings

Figure 66 through Figure 69 represent synchronous waveforms, and Table 100 and Table 101 provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x01;
- COM.FMC_WaitSetupTime = 0x03;
- COM.FMC_HoldSetupTime = 0x02;
- COM.FMC_HiZSetupTime = 0x01;
- ATT.FMC_SetupTime = 0x01;
- ATT.FMC_WaitSetupTime = 0x03;
- ATT.FMC_HoldSetupTime = 0x02;
- ATT.FMC_HiZSetupTime = 0x01;
- Bank = FMC_Bank_NAND;
- MemoryDataWidth = FMC_MemoryDataWidth_16b;
- ECC = FMC_ECC_Enable;
- ECCPageSize = FMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

Table 102. SDRAM read timings⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_{su(SDCLKH_Data)}$	Data input setup time	3.5	-	
$t_{h(SDCLKH_Data)}$	Data input hold time	1.5	-	
$t_{d(SDCLKL_Add)}$	Address valid time	-	4	
$t_{d(SDCLKL_SDNE)}$	Chip select valid time	-	0.5	
$t_{h(SDCLKL_SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL_SDNRAS)}$	SDNRAS valid time	-	0.5	
$t_{h(SDCLKL_SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL_SDNCAS)}$	SDNCAS valid time	-	0.5	
$t_{h(SDCLKL_SDNCAS)}$	SDNCAS hold time	0	-	

1. Guaranteed by characterization results.

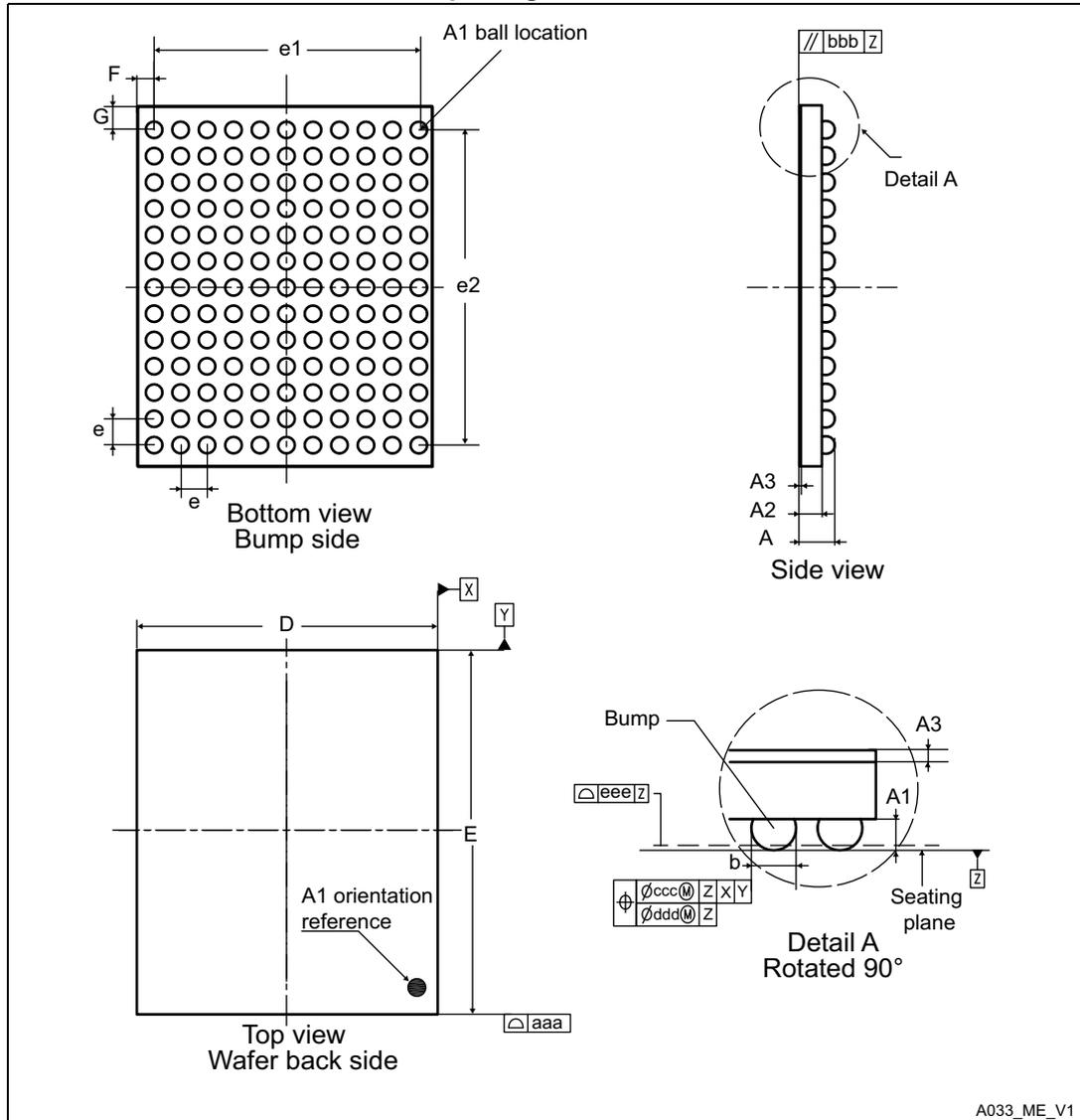
Table 103. LPDDR SDRAM read timings⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_{su(SDCLKH_Data)}$	Data input setup time	3	-	
$t_{h(SDCLKH_Data)}$	Data input hold time	1.5	-	
$t_{d(SDCLKL_Add)}$	Address valid time	-	3.5	
$t_{d(SDCLKL_SDNE)}$	Chip select valid time	-	0.5	
$t_{h(SDCLKL_SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL_SDNRAS)}$	SDNRAS valid time	-	0.5	
$t_{h(SDCLKL_SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL_SDNCAS)}$	SDNCAS valid time	-	0.5	
$t_{h(SDCLKL_SDNCAS)}$	SDNCAS hold time	0	-	

1. Guaranteed by characterization results.

6.3 WLCSP143, 4.539x 5.849 mm, 0.4 mm pitch wafer level chip scale package information

Figure 85. WLCSP143, 4.539x 5.849 mm, 0.4 mm pitch wafer level chip scale package outline



1. Drawing is not to scale.

Table 115. WLCSP143, 4.539x 5.849 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-